



#### SINGLE N-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
	8mΩ @ V <sub>GS</sub> = 10V	12A
20V	9mΩ @ V <sub>GS</sub> = 4.5V	10A
	12mΩ @ V <sub>GS</sub> = 2.5V	8A

### **Features**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Description and Applications**

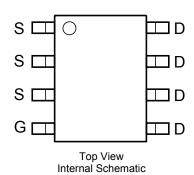
This MOSFET has been designed to minimize the on-state resistance (RDS(on)) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

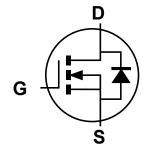
- Backlighting
- **Power Management Functions**
- DC-DC Converters

### **Mechanical Data**

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.074 grams (approximate)







Equivalent circuit

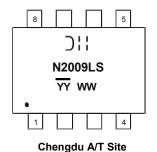
### Ordering Information (Note 4)

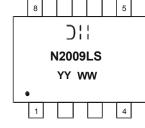
Part Number	Case	Packaging
DMN2009LSS-13	SO-8	2500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**





Shanghai A/T Site

);; = Manufacturer's Marking N2009LS = Product Type Marking Code YYWW = Date Code Marking YY or  $\overline{YY}$  = Year (ex: 13 = 2013) WW = Week (01 - 53)

YY = Date Code Marking for SAT (Shanghai Assembly/ Test site) YY = Date Code Marking for CAT (Chengdu Assembly/ Test site)



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			$V_{DSS}$	20	V
Gate-Source Voltage			$V_{GSS}$	±12	V
Drain Current (Note 5)	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	12 9.6	А
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	42	А

# Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	2	W
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	62.5	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

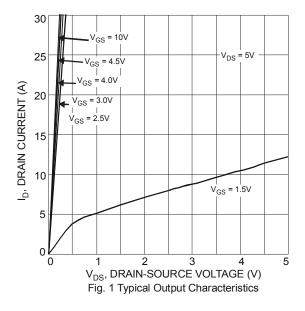
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

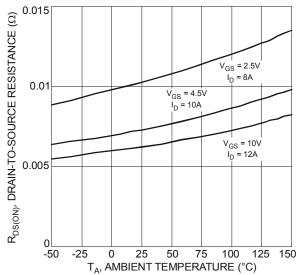
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)			_	_	_		
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.5	_	1.2	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
			_	8		V <sub>GS</sub> = 10V, I <sub>D</sub> = 12A	
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>		_	9	mΩ	$V_{GS} = 4.5V, I_D = 10A$	
			_	12		$V_{GS} = 2.5V, I_D = 8A$	
Forward Transconductance	g <sub>fs</sub>		27	_	S	$V_{DS} = 5V, I_{D} = 6.5A$	
Diode Forward Voltage	$V_{SD}$	0.5	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 3A$	
DYNAMIC CHARACTERISTICS (Note 8)			_	_	_		
Input Capacitance	C <sub>iss</sub>	_	2555	_	pF		
Output Capacitance	Coss	_	523	_	pF	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	496	_	pF		
Gate Resistance	$R_G$	_	1.1	_	Ω	$V_{GS} = 0V V_{DS} = 0V, f = 1MHz$	
SWITCHING CHARACTERISTICS (Note 8)			_	_	_		
Total Gate Charge			28.9			$V_{DS} = 10V, V_{GS} = 4.5V, I_{D} = 12A$	
Total Gate Charge	Qg		58.3		nC	$V_{DS} = 10V$ , $V_{GS} = 10V$ , $I_{D} = 12A$	
Gate-Source Charge	Q <sub>gs</sub>		3.7	_	$V_{DS} = 10V, V_{GS} = 10V, I_D = 1$		
Gate-Drain Charge	$Q_{gd}$		11.4			$V_{DS} = 10V, V_{GS} = 10V, I_D = 12A$	

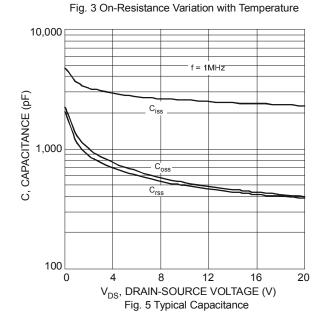
Notes:

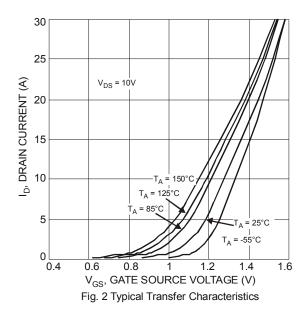
- 5. Device mounted on 2 oz, FR-4 PCB, with  $R_{\theta JA}$  = 62.5°C/W
- Pulse width ≤10μS, Duty Cycle ≤1%.
  Short duration pulse test used to minimize self-heating effect.
  Guaranteed by design. Not subject to product testing.

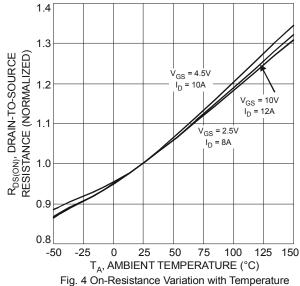












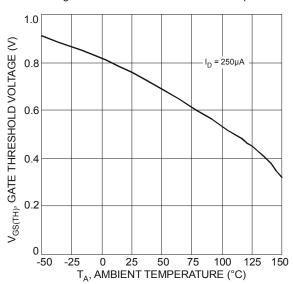
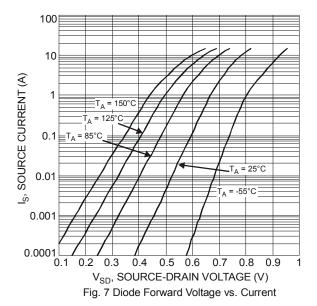
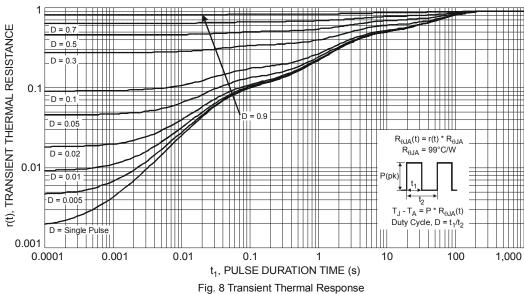


Fig. 6 Gate Threshold Variation vs. Ambient Temperature

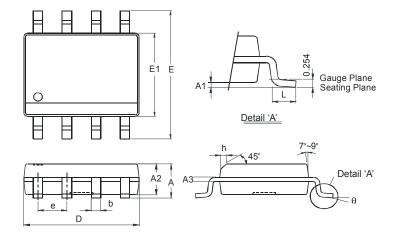






# Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

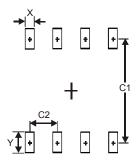


SO-8					
Dim	Min	Max			
Α	-	1.75			
<b>A</b> 1	0.10	0.20			
A2	1.30	1.50			
A3	0.15	0.25			
b	0.3	0.5			
D	4.85	4.95			
Е	5.90	6.10			
E1	3.85	3.95			
е	1.27 Typ				
h	- 0.35				
L	0.62	0.82			
θ	0°	8°			
All Dimensions in mm					



# Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Х	0.60
Υ	1.55
C1	5.4
C2	1.27

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